



#18/E
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Sunder
PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

Tomoyoshi KUSHIDA

Application No.: 09/435,766

Filed: November 8, 1999

For: SEMICONDUCTOR DEVICE

Group Art Unit: 2811

Examiner: S. Loke

Docket No.: 104361

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PRELIMINARY AMENDMENT

Director of the U.S. Patent and Trademark Office
Washington, D. C. 20231

Sir:

Prior to initial examination, please amend the above-identified application as follows:

IN THE CLAIMS:

Please replace claims 1 and 4 as follows:

1. (Four Times Amended) A bipolar semiconductor device comprising:

E' sub A
a drain electrode;

a drain region having a first conductive type semiconductor and disposed on the drain electrode;

figs. 1A, 1B,
5,
a drift region having a second conductive type semiconductor different from the first conductive type semiconductor of the drain region and disposed on the drain region;

6, 7,
lines 3-8
a channel region having the second conductive type semiconductor and disposed on the drift region;

a gate region surrounding at least a part of the channel region via an insulation film, the gate region having the first conductive type semiconductor;